

FEATURES

- 1). Interdigitated amplifying gates
- 2). Fast turn-on and high di/dt
- 3). Low switching losses

$I_{T(AV)}$	2606 A
V_{DRM}/V_{RRM}	1900~2500 V
t_q	50~80 μ s
I_{TSM}	33.8 KA
I^2t	5712 $10^3 A^2S$



TYPICAL APPLICATIONS

- 1). Inductive heating
- 2). Electronic welders
- 3). Self-commutated inverters

THE MAIN PARAMETERS

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled, $T_{hs}=55^{\circ}C$	125			2749	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}, t_p=10ms$ $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 100V$	125	1900		2500	V
I_{DRM} I_{RRM}	Repetitive peak off-state current Repetitive peak reverse current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			200	mA
I_{TSM} I^2t	Surge on-state current I^2T for fusing coordination	10ms half sine wave $V_R = 0.6V_{RRM}$	125			33.8 5712	KA $A^2s \cdot 10^3$
V_{TO}	Threshold voltage		125			1.48	V
r_T	On-state slop resistance		125			0.15	m Ω
V_{TM}	Peak on-state voltage	$I_{TM}=4000A, F=40KN$	125			2.08	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	V/ μ s
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 3000A, Gate pulse $t_r \leq 0.5 \mu$ s $I_{GM}=1.5A$	125			1000	A/ μ s
I_{rm}	Reverse recovery current	$I_{TM}=2000A, t_p=1000 \mu$ s, di/dt=-20A/ μ s, VR=50V	125		187		A
t_{rr}	Reverse recovery time				11.2		μ s
Q_{rr}	Recovery charge				1049	1200	μ C
t_q	Circuit commutated turn-off time	$I_{TM}=2000A, t_p=1000 \mu$ s, $V_R=50V$ dv/dt=30V/ μ s, di/dt=-20A/ μ s	125	50		80	μ s
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	40		450	mA
V_{GT}	Gate trigger voltage			0.9		4.5	V
I_H	Holding current			20		1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-h)}$	Thermal resistance Junction to heatsink	At 180° sine, double side cooled Clamping force 40KN				0.011	$^{\circ}C/W$
F_m	Mounting force			35		47	KN
T_{stg}	Stored temperature			-40		140	$^{\circ}C$
W_t	Weight				1100		g
Size	Package box size	160 × 145 × 65					mm

PERFORMANCE CURVES FIGURE

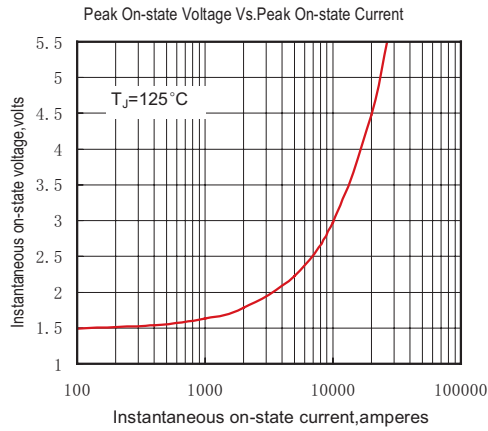


Fig.1

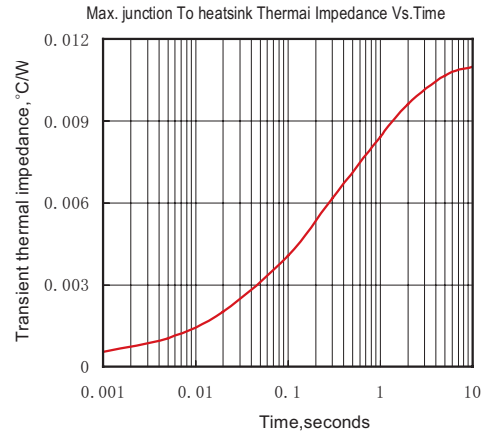


Fig.2

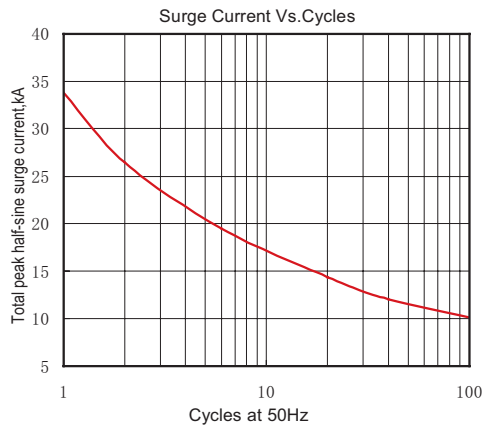


Fig.3

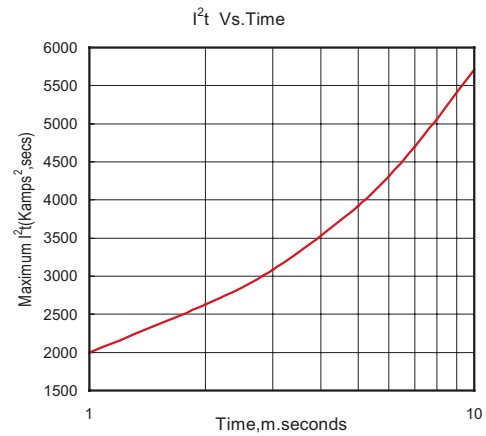


Fig.4

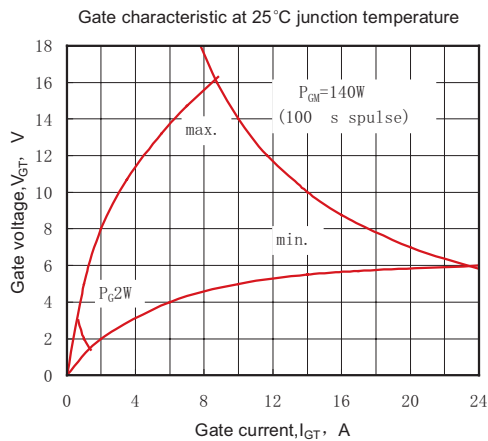


Fig.5

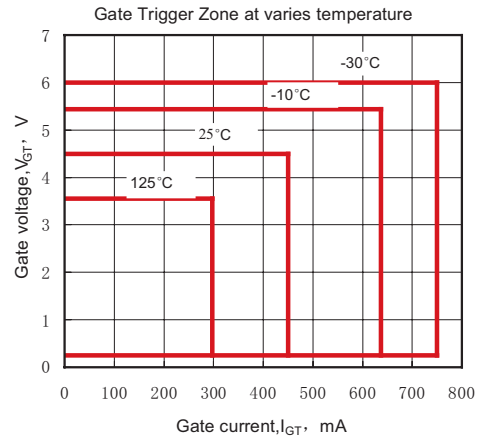
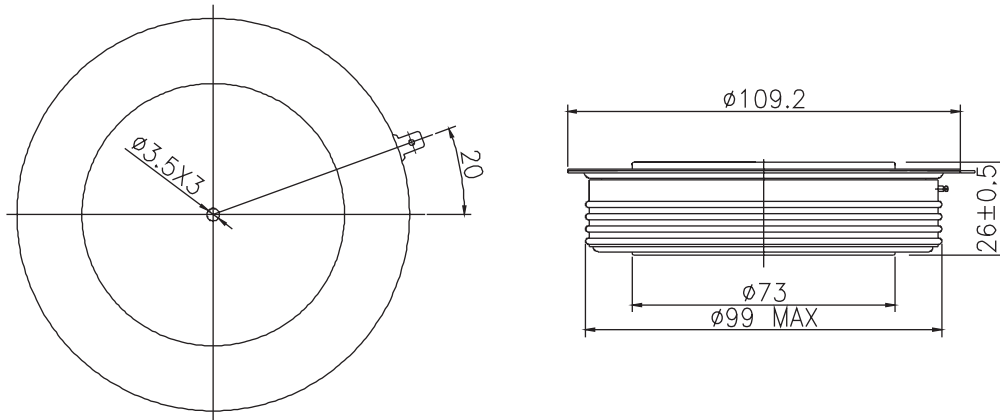


Fig.6

OUTLINE



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